

Fig.3

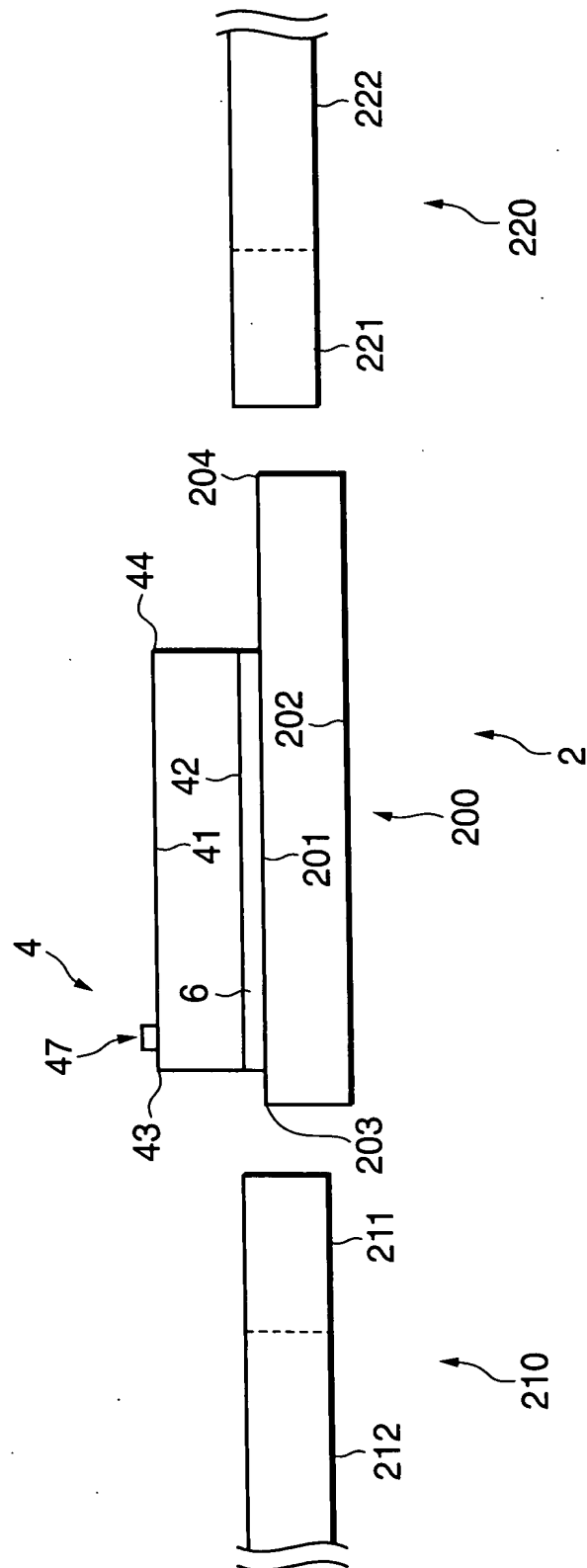


Fig. 4

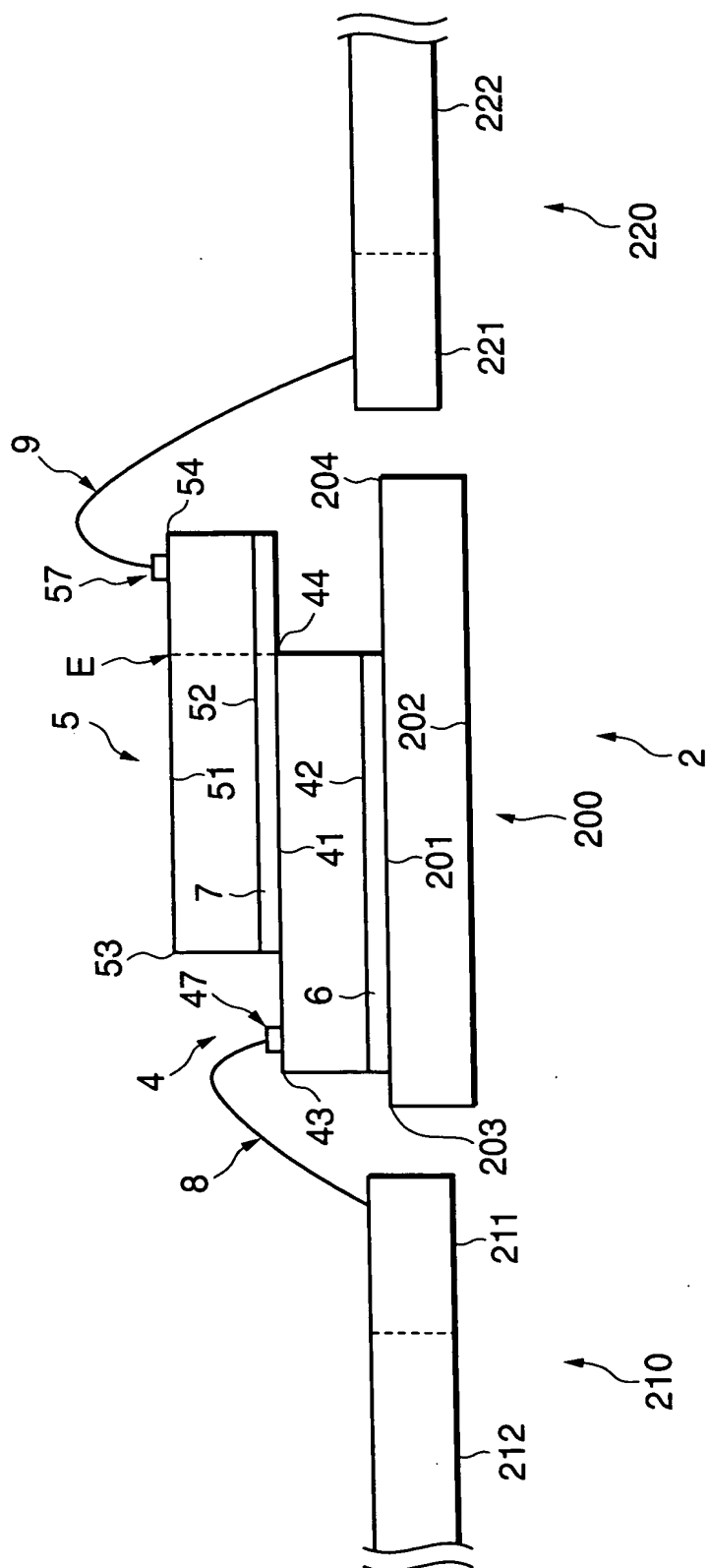


Fig.6

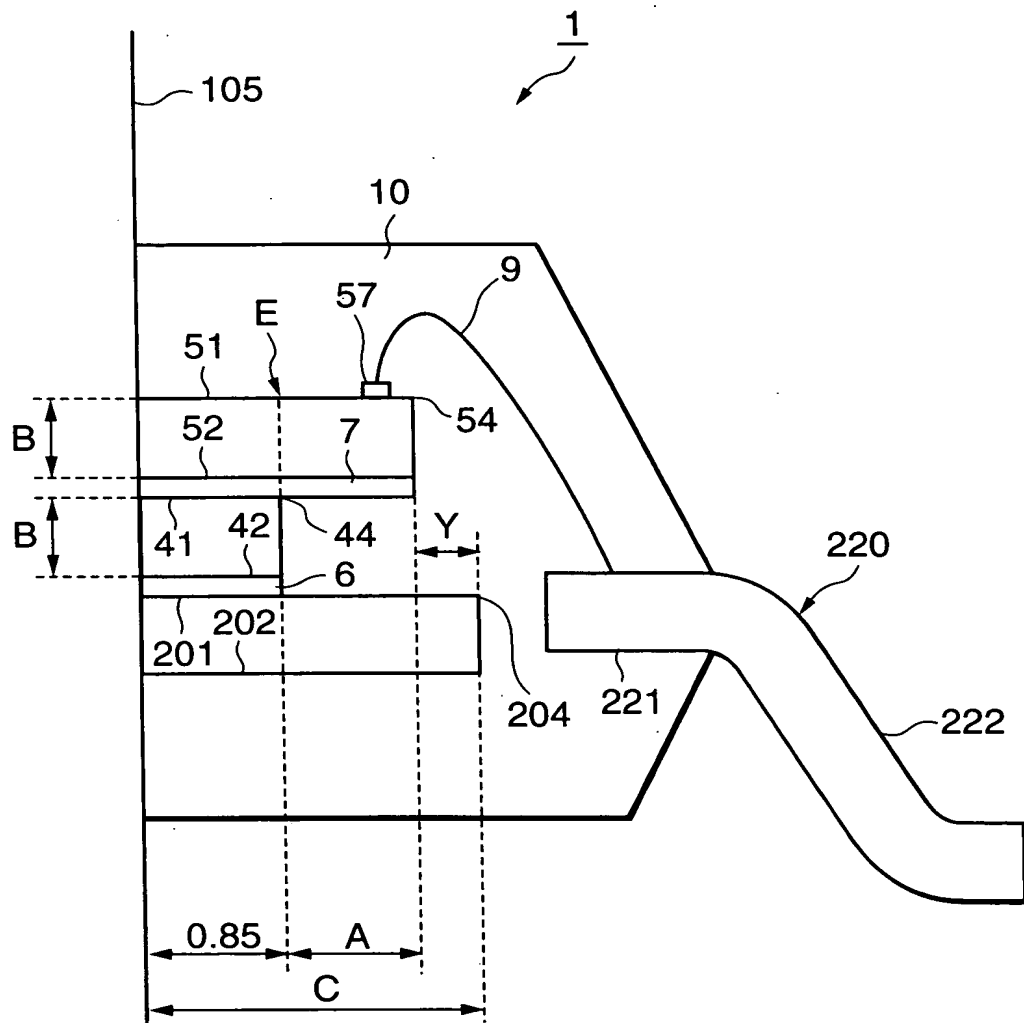


Fig.7(a)

MATERIAL	ELASTIC MODULUS (kg/mm ²)	POISSON'S RATIO
BASE MATERIAL OF SEMICONDUCTOR CHIPS	17335	0.07
LEAD FRAME	14800	0.3
RESIN ENCAPSULATING OR SEALING BODY	80	0.24
ADHESIVE	240	0.3

Fig.7(b)

THE RATIO TO LENGTH OF SEMICONDUCTOR CHIPS			
CONDITIONS ITEM	1	2	3
AMOUNT A OF DISPLACEMENT	0.1	0.2	0.3
THICKNESS B OF CHIP	0.02	0.04	0.06
HALF C OF LENGTH OF DIE PAD	0.7	1	1.3

Fig.8

NUMBER OF EXPERIMENTS	A	B	C	MAXIMUM STRESS (ALL)	MAXIMUM STRESS (EDGE PORTION)
1	1	1	1	9.1	2.6
2	1	2	2	6.9	2.9
3	1	3	3	3	1.8
4	2	1	2	9.2	1.5
5	2	2	3	7	3.1
6	2	3	1	4.6	4.4
7	3	1	3	9.2	1
8	3	2	1	6.4	5.3
9	3	3	2	4.6	3.9

MEASURE OF STRESS : kg/mm²

Fig.9(a)

LEVEL-BY-LEVEL AVERAGE OF MAXIMUM STRESS (ALL) (kg/mm ²)							
A1	A2	A3	B1	B2	B3	C1	C3
6.3	6.9	6.7	9.2	6.8	4.1	6.7	6.4

Fig.9(b)

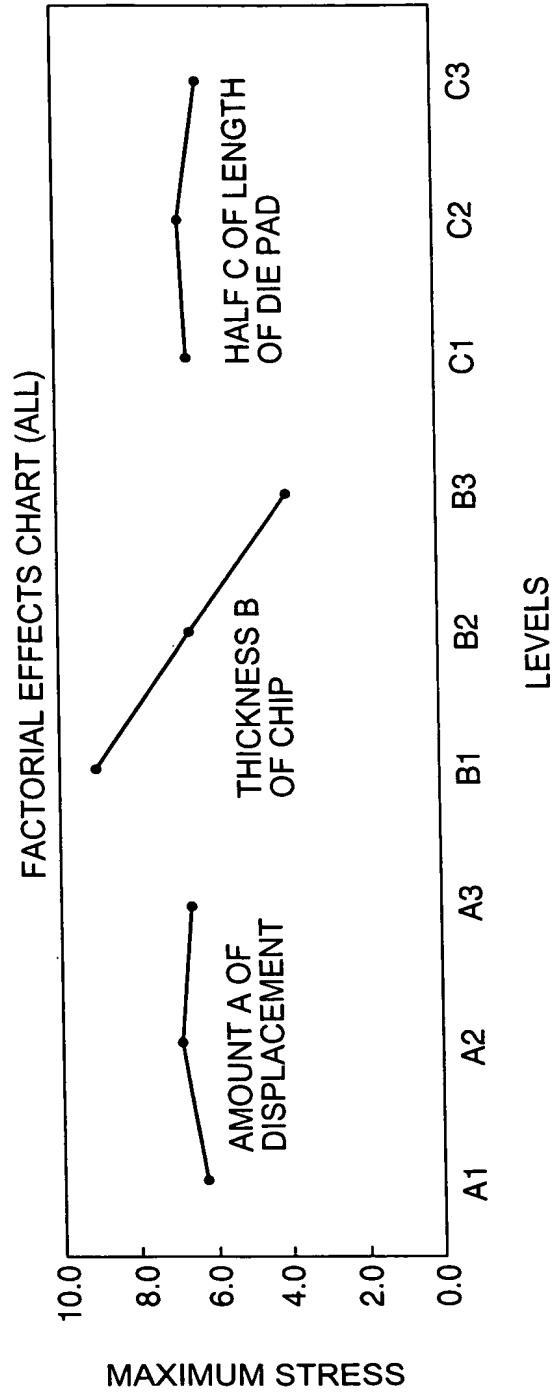


Fig.10(a)

LEVEL-BY-LEVEL AVERAGE OF MAXIMUM STRESS (EDGE PORTION) (kg/mm ²)								
A1	A2	A3	B1	B2	B3	C1	C2	C3
2.4	3.0	3.4	1.7	3.8	3.4	4.1	2.8	2.0

Fig.10(b)

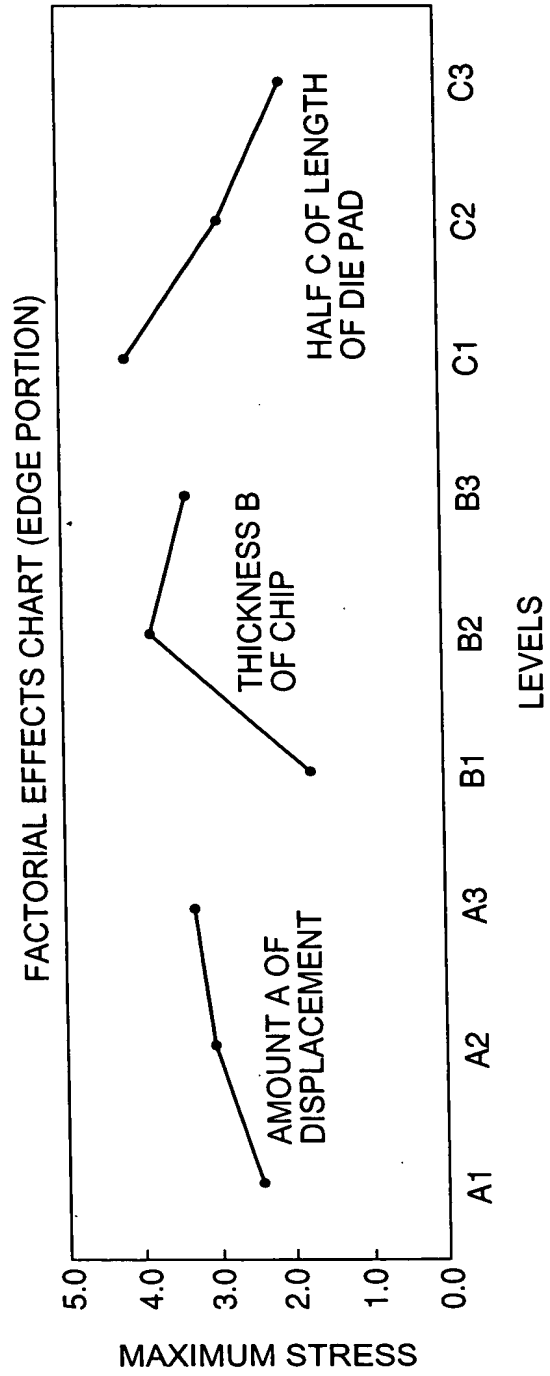
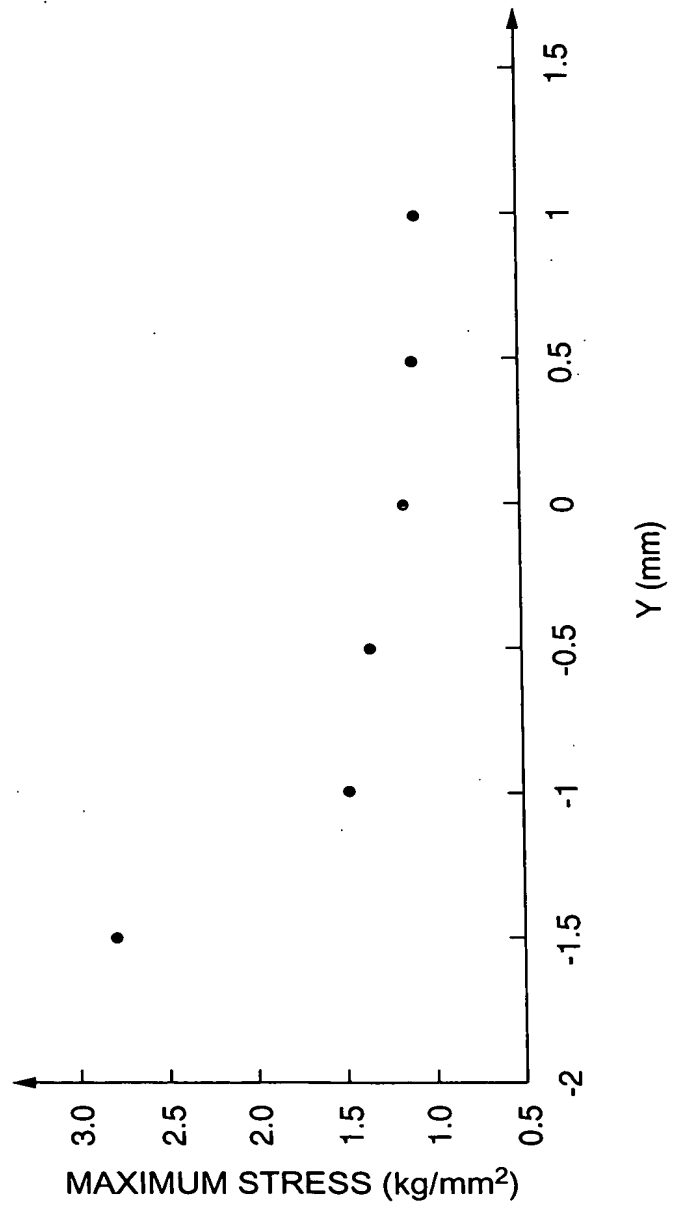


Fig.11



A cross-sectional view of a semiconductor device 1. The device features a substrate 10 with a central region 200. A first layer 201 is formed on the substrate 10, with a central opening 207. A second layer 202 is formed on top of the first layer 201. A third layer 210 is formed on top of the second layer 202, with a central opening 212. A fourth layer 220 is formed on top of the third layer 210, with a central opening 222. The device includes various components labeled with reference numerals: 1 (device), 2 (top surface), 4 (top surface of layer 201), 5 (top surface of layer 202), 6 (top surface of layer 202), 7 (top surface of layer 210), 8 (top surface of layer 210), 9 (top surface of layer 220), 10 (substrate), 41 (layer 201), 42 (layer 202), 43 (layer 210), 44 (layer 220), 47 (layer 201), 51 (layer 202), 52 (layer 210), 53 (layer 210), 54 (layer 220), 57 (layer 220), 201 (layer 201), 202 (layer 202), 207 (opening in layer 201), 210 (layer 210), 211 (layer 210), 212 (opening in layer 210), 220 (layer 220), 221 (layer 220), 222 (opening in layer 220).

[illegible]

Fig.13

SHAPE OF DIE PAD SECTION	STRESS (kg/mm ²)
SLITS	4.0
NO SLIT	0.1

Fig.14(b)

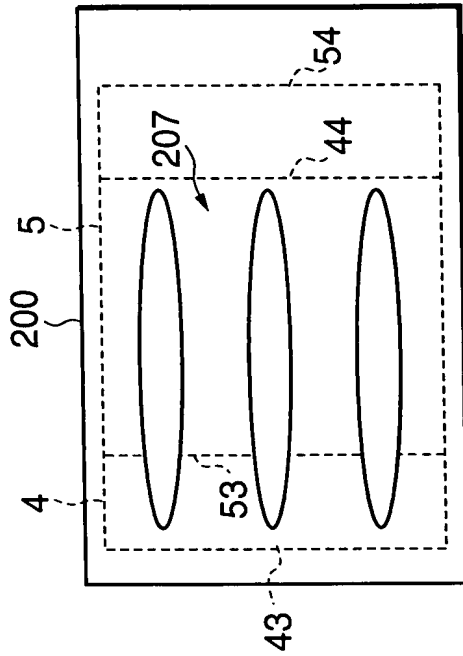


Fig.14(d)

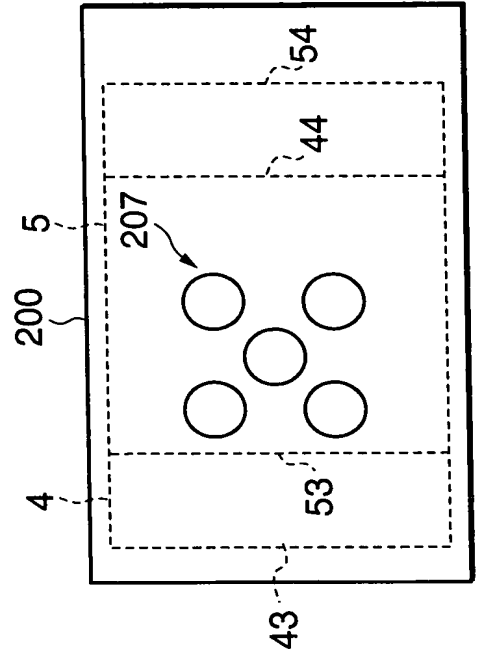


Fig.14(a)

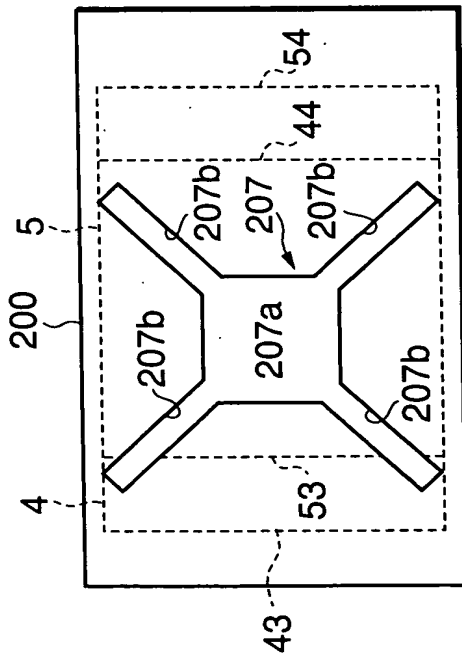


Fig.14(c)

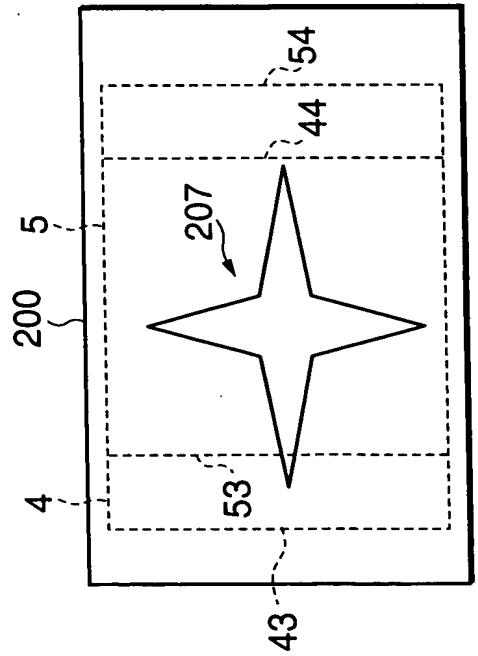


Fig. 15

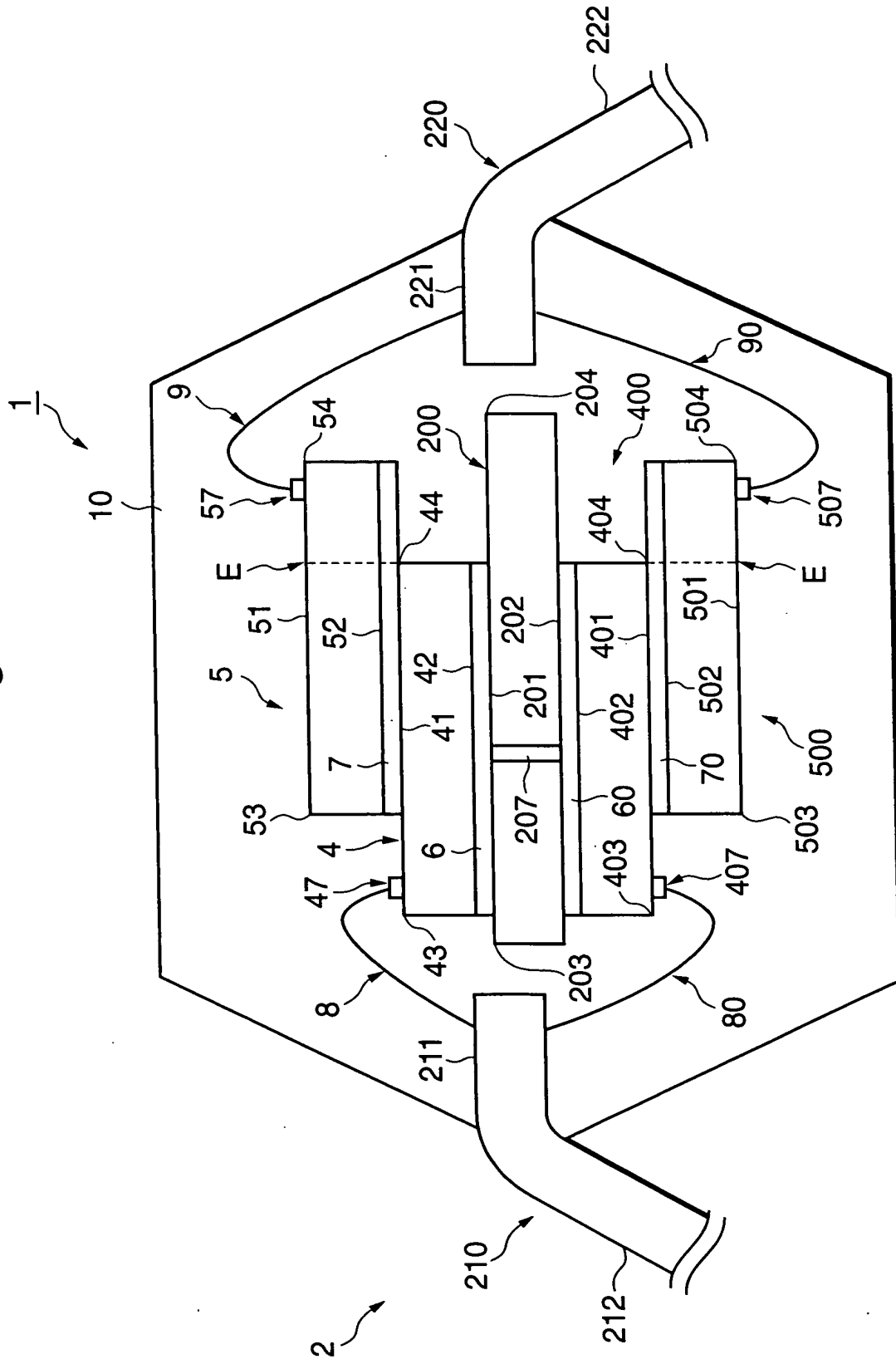
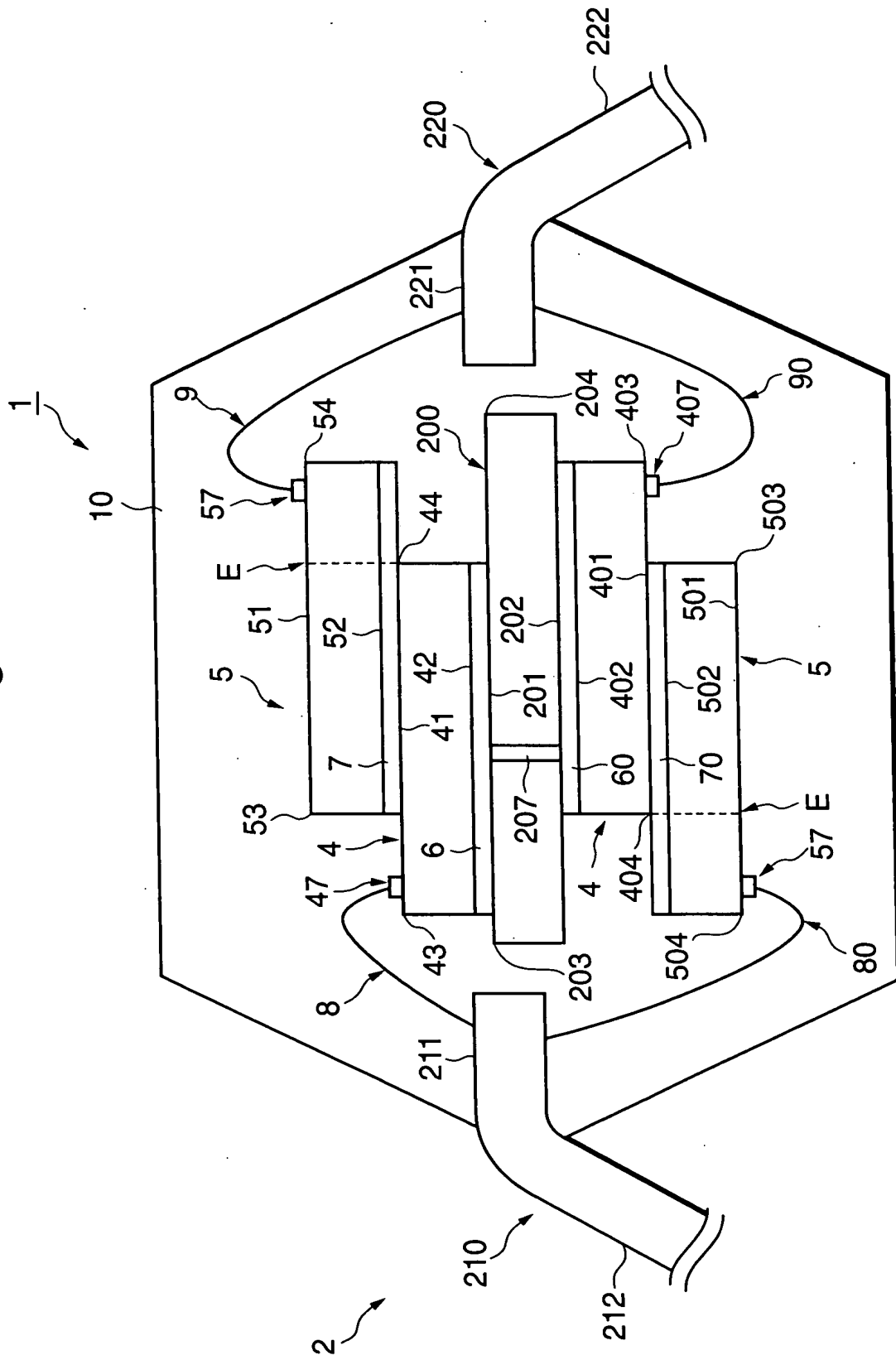


Fig. 16



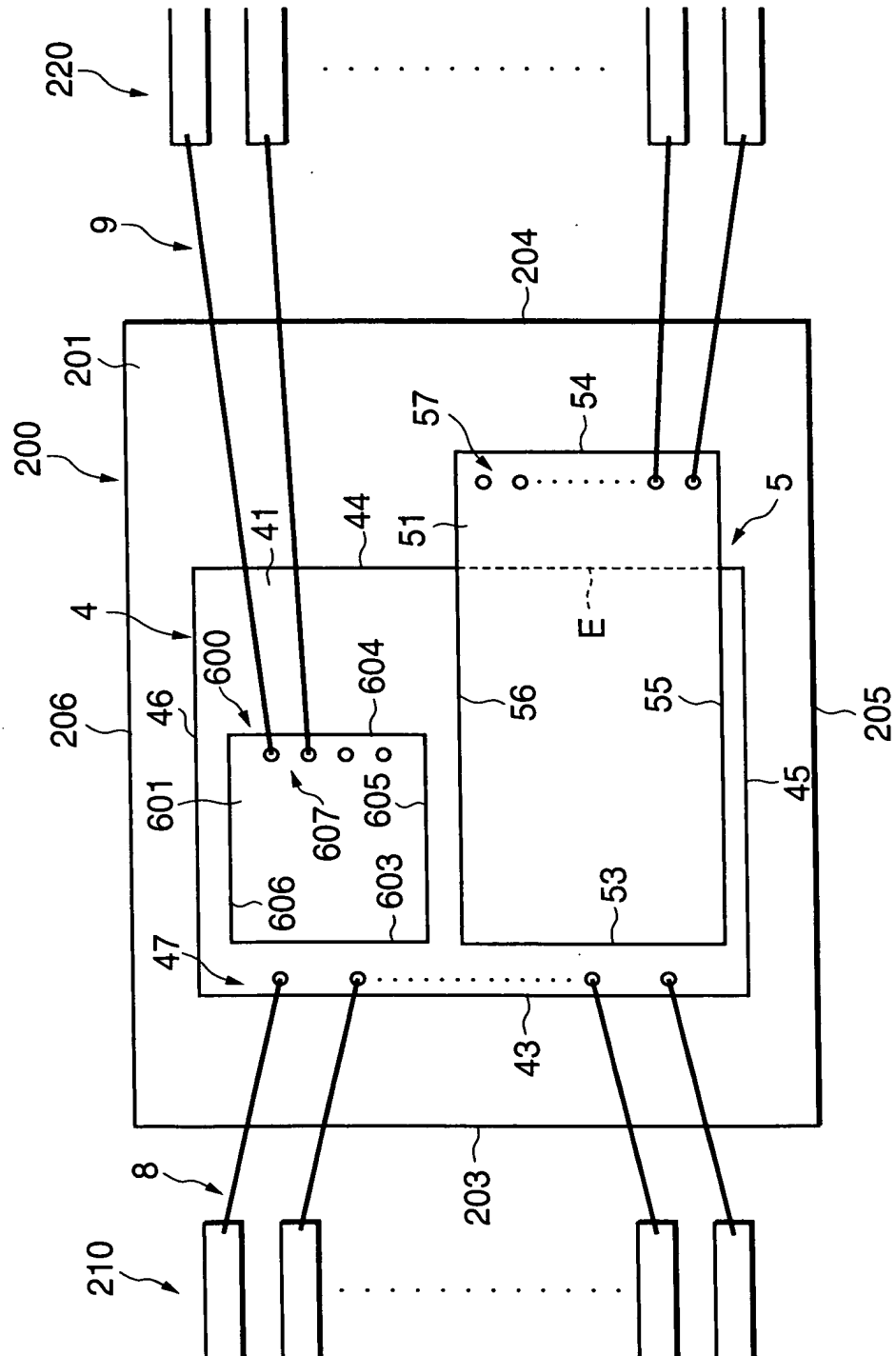


Fig.18

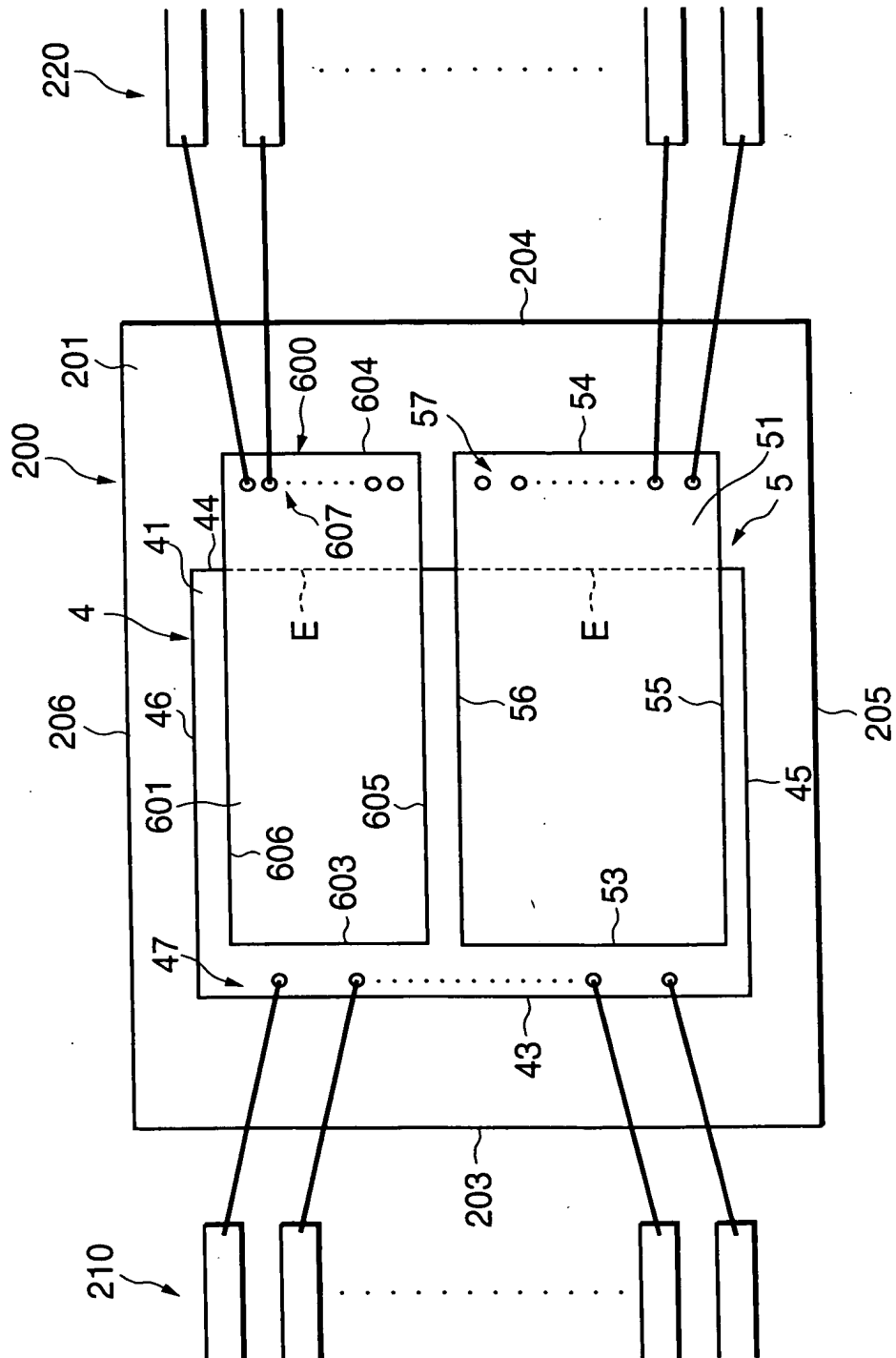


Fig.19

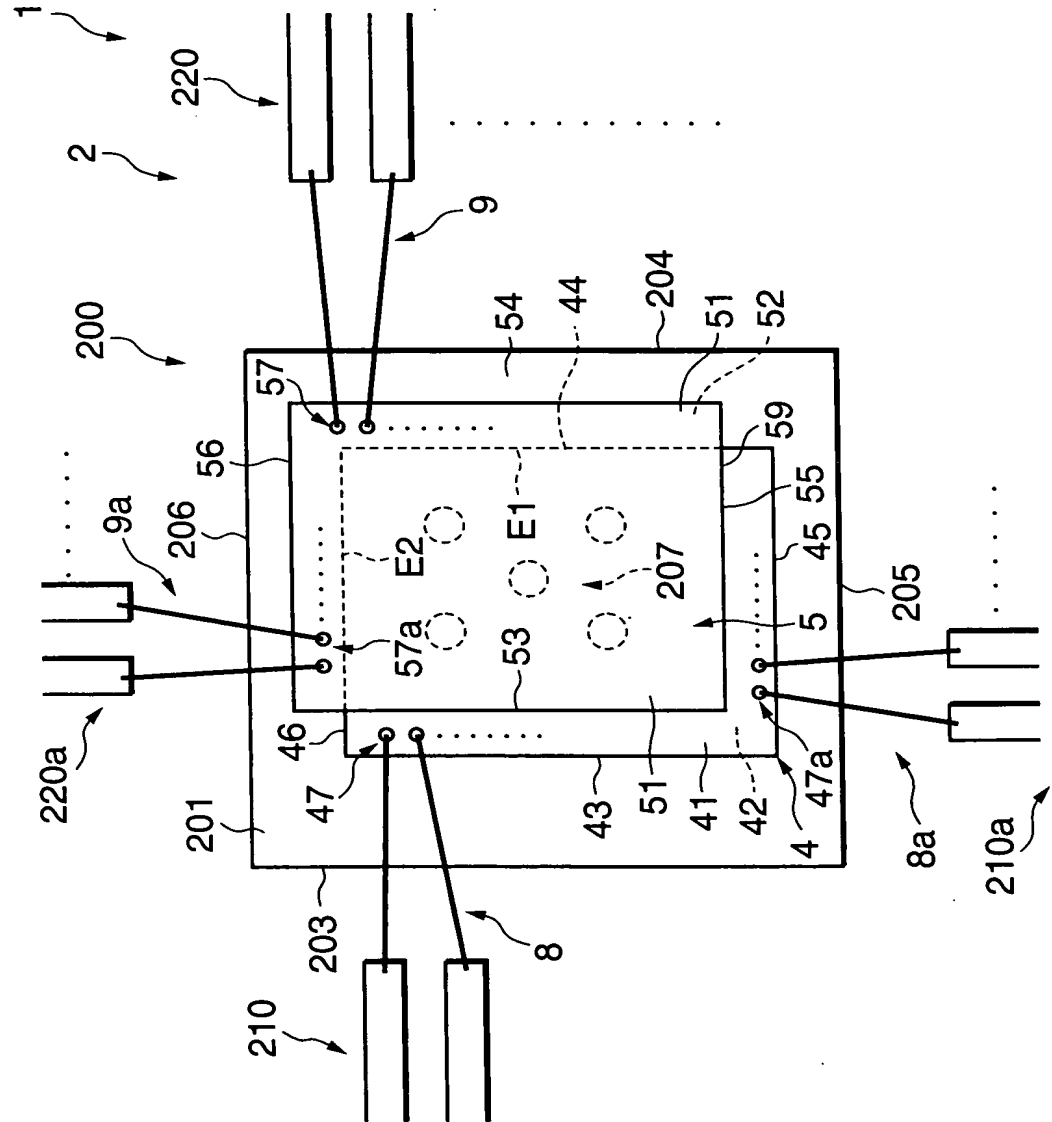


Fig.20

